INTERNATIONAL STANDARD



QC 750116

First edition 2000-04

Semiconductor devices - Discrete devices -

Part 4-2: Microwave diodes and transistors – Integrated-circuit microwave amplifiers – Blank detail specification

Dispositifs à semiconducteurs - Dispositifs discrets -

Partie 4-2 Diodes et transistors hyperfréquences – Amplificateurs hyperfréquences pour circuits intégrés – Spécification particulière-cadre



Reference number IEC 60747-4-2:2000(E)

Numbering

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Consolidated publications

Consolidated versions of some IEC publications including amendments are available. For example, edition numbers 1.0, 1.1 and 1.2 refer, respectively, to the base publication, the base publication incorporating amendment 1 and the base publication incorporating amendments 1 and 2.

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The technical content of IEC publications is kept under constant review by the IEC thus ensuring that the content reflects current technology.

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- IEC web site*
- Catalogue of IEC publications Published yearly with regular updates (On-line catalogue)*
- IEC Bulletin Available both at the IEC web site* and as a printed periodical

Terminology, graphical and letter symbols

For general terminology, readers are referred to IEC 60050: International Electrotechnical Vocabulary (IEV).

ps://standards.il/For graphical symbols, and letter symbols and signs approved by the IEC for C-60747-4-2-2000 general use, readers are referred to publications IEC 60027: Letter symbols to be used in electrical technology, IEC 60417: Graphical symbols for use on equipment. Index, survey and compilation of the single sheets and IEC 60617: Graphical symbols for diagrams.

See web site address on title page.

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Commission Electrotechnique Internationale International Electrotechnical Commission Международная Электротехническая Комиссия



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INTERNATIONAL ELECTROTECHNICAL COMMISSION

SEMICONDUCTOR DEVICES – DISCRETE DEVICES –

Part 4-2: Microwave diodes and transistors – Integrated-circuit microwave amplifiers – Blank detail specification

FOREWORD

- 1) The IEC (International Electrotechnical Commission) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of the IEC is to promote international cooperation on all questions concerning standardization in the electrical and electronic tields. To this end and in addition to other activities, the IEC publishes International Standards. Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. The IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
- 2) The formal decisions or agreements of the IEC on technical matters express as nearly as possible, an international consensus of opinion on the relevant subjects since each redunical committee has representation from all interested National Committees.
- 3) The documents produced have the form of recommendations for international use and are published in the form of standards, technical specifications, technical reports or guides and they are accepted by the National Committees in that sense.
- 4) In order to promote international unification, IEC National Committees undertake to apply IEC International Standards transparently to the maximum extent possible in their national and regional standards. Any divergence between the IEC Standard and the corresponding national or regional standard shall be clearly indicated in the latter.
- 5) The IEC provides no marking procedure to indicate its approval and cannot be rendered responsible for any equipment declared to be in conformity with one of its standards

6) Attention is drawn to the possibility that some of the elements of this International Standard may be the subject of patent rights. The IEC shall not be held responsible for dentifying any or all such patent rights.

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International Standard NEC 60747-4-2 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices.

This standard is a blank detail specification for integrated-circuit microwave amplifiers.

The text of this standard is based on the following documents:

FDIS	Report on voting
47E/142/FDIS	47E/148/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has not been drafted in complete accordance with the ISO/IEC Directives, Part 3.

The QC number that appears on the front cover of this publication is the specification number in the IEC Quality Assessment System for Electronic Components (IECQ).

A bilingual version of this standard may be issued at a later date.

The committee has decided that the contents of this publication will remain unchanged until 2005. At this date, the publication will be

- reconfirmed;
- withdrawn;
- replaced by a revised edition, or
- amended.

Other IEC publications quoted in this standard:

Publication Nos. IEC 60068-2-17:1994, Basic environmental testing procedures – Part 2: Tests – Test Q: Sealing

IEC 60747-1:1983, Semiconductor devices – Discrete devices – Part 1: General

IEC 60747-4:1991, Semiconductor devices – Discrete devices – Part 4: Microwave diodes and transistors

IEC 60747-10:1991, Semiconductor devices – Part 10: Generic specification for discrete devices and integrated circuits

IEC 60748-1:1984, Semiconductor devices - Integrated circuits - Part 1: General

IEC 60748-11:1990, Semiconductor devices - Integrated circuits - Part 11: Sectional specification for semiconductor integrated circuit excluding hybrid circuits

IEC 60749:1996, Semiconductor devices - Mechanical and climatic test methods

IEC QC 001002:1986, Rules of Procedure of the IEC Quality Assessment System for Electronic Components (IECQ)

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SEMICONDUCTOR DEVICES – DISCRETE DEVICES –

Part 4-2: Microwave diodes and transistors – Integrated-circuit microwave amplifiers – Blank detail specification

INTRODUCTION

The IEC Quality Assessment System for Electronic Components is operated in accordance with the statutes of the IEC and under the authority of the IEC. The object of this system is to define quality assessment procedures in such a manner that electronic components released by one participating country as conforming with the requirements of an applicable specification are equally acceptable in all other participating countries without the need for further testing.

This blank detail specification is one of a series of blank detail specifications for semiconductor devices and shall be used with the following IEC publications:

IEC 60747-10/QC 700000:1991, Semiconductor devices Part 10: Generic specification for discrete devices and integrated circuits

IEC 60748-11/QC 790100:1990, Semiconductor devices –/Integrated sircuits – Part 11: Sectional specification for semiconductor integrated circuits excluding hybrid sircuits

Required information

Numbers shown in brackets on this and the following pages correspond to the following items of required information, which should be entered in the spaces provided.

Identification of the detail specification

- [1] The name of the national standards organization under whose authority the detail specification is issued.
- htt [2] / The IECQ number of the detail specification. 168-f0cd-4c48-8559-0fdcb8eff3f0/jec-60747-4-2-2000
 - [3] The numbers and issue numbers of the generic and sectional specifications.
 - [4] The national number of the detail specification, date of issue and any further information required by the national system.

Identification of the component

- [5] Main function and type number.
- [6] Information on typical construction (materials, main technology) and package. If the device has several kinds of derivative products, these differences shall be indicated, for example features in the comparison table.

For electrostatic sensitive devices, a note of caution regarding electrostatic sensitivity shall be added in the detail specification.

- [7] Outline drawing, terminal identification, marking and/or reference to the relevant document for outlines.
- [8] Category of assessed quality according to 2.6 of the generic specification.
- [9] Reference data.

[Throughout this standard, the texts given in square brackets are intended to serve as guidance for the specification writer and shall not be included in the detail specification.]

[When confusion may arise as to whether a paragraph is meant as an instruction to the writer or not, it shall be given in brackets.]

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1 Marking and ordering information

1.1 Marking

[See 2.5 of generic specification.

The detail specification shall state the information marked for the relevant types, such as letters, figures and/or codes.

When the marking contains items other than those specified in 2.5 of the generic specification, such as used for the manufacturer's internal use, this should be indicated.

If all the information has already appeared in box [7] on the front page, this shall be indicated.]

1.2 Ordering information

[The following minimum information is necessary to order a specific device, unless otherwise specified:

- precise type reference (and nominal voltage value, if required);
- IECQ reference of detail specification with issue number and/or date when relevant;
- category of assessed quality as defined in clause 9 of the sectional specification and, if required, screening sequence as defined in clause 8 of the same;
- packaging for delivery;
- any other particulars.]

2 Application-related description

[Information regarding application in equipments or in circuits, and the relation with the associated devices shall be given here. See IEC 60748-1, Chapter VI.]

3 Specification of the function

[Information regarding the function of the device shall be given here. Items to be given here shall be selected from NEC 60748-1, Chapter VI.]

4 Limiting values (absolute maximum rating system)

These values apply over the operating temperature range, unless otherwise specified.

[Repeat only subclause numbers used, together with title. Any additional values shall be given at the appropriate place, but without subclause number.]

[Curves shall preferably be given in clause 9 of the detail specification.]

Categories Type A: low-noise Type B: auto-gain control Type C: limiting Type D: power

Subclause	Limiting value	Symbol	Тур	e A	Туре В		Туре С		Тур	e D
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
4.1	Ambient or case temperature	$T_{\rm amb}$ or $T_{\rm case}$	×	×	×	×	×	×	×	×
4.2	Storage temperature	$ au_{stg}$	×	×	×	×	×	×	×	×
4.3	Power supply voltage(s) [note 1]	V _{xxi}		×		×		×		×
4.4	Power supply current(s) [note 1]	I _{xxi}		×		×		×		×
4.5	Terminal voltage(s) [notes 1 and 2]	V _{xxi}		×		×	\bigcirc			×
4.6	Terminal current(s) [notes 1 and 2]	I _{xxi}		×	\searrow	×				×
4.7	Input power	$P_{\sf in}$	1	\sim			\sim	×		×
4.8	Channel temperature	T _{ch} ; T _j		×			$\boldsymbol{\mathcal{V}}$	×		×
4.9	Power dissipation [note 3]	P _{tot}	Ω	X				×		×

NOTE 1 'xx' is the symbol of a terminal and 'i' is the terminal number of the same kind, such as V_{GG1} for the voltage of the first gate terminal and I_{DD2} for the current of the second drain terminal.

NOTE 2 Where appropriate.

NOTE 3 Maximum value over the specified range of operating ambient or reference-point temperatures. Any special requirements for ventilation and/or mounting shall be stated.

5 Operating conditions (within the specified operating ambient or case temperature range)

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Operating conditions are specified in the relevant measuring methods.

See 13.2 of this standard for inspection requirements.

- 5.1 Power supply voltage
- 5.2 Power supply current
- 5.3 Input power (where appropriate)
- 5.4 Voltage and/or current at another or other terminal(s) (where appropriate)
- 5.5 External element(s) (where appropriate)
- 5.6 Operating frequency range
- 5.7 Operating temperature range

6 Electrical characteristics

[Repeat only subclause numbers used, with title. Any additional characteristics shall be given at the appropriate place but without subclause number.]

[When several devices are defined in the same detail specification, the relevant values shall be given on successive lines whilst avoiding the repetition of identical values.]

[Curves should preferably be given under clause 9 of the detail specification.]

The following characteristics apply over the full operating ambient temperature range, unless otherwise stated.

[Where the stated performance of the circuit varies over the operating ambient temperature range, the values of the appropriate characteristics shall be stated at 25 °C and at the extremes of the operating temperature range.]

6.1 Static characteristics

Sub-	Characteristics and conditions at	Symbol	Тур	A pe	Тур	e B	Тур	e C	Тур	e D	Tested
clause	T_{amb} or $T_{case} = 25 \text{ °C}$, unless otherwise specified (see clause 4 of the generic specification)	\wedge	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
6.1.1	Power supply current(s): value(s) at specified supply voltage(s)	/xxi	×	×	×	×	×	×	×	×	A3
6.1.2	Thermal resistance channel to case: value at specified <i>T</i> _{case}	R _{th(j-c)}			sit		ai	×		×	C2d
			5	$\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{\mathbf{$	vie	W					

6.2 AC characteristics

Sub- clause Characteristics and conditions a T_{amb} or $T_{case} = 25$ °C, unless otherwise specified (see clause of the generic specification)	Symbol	Туре А		Type B		Туре С		Type D		Tested	
	otherwise specified (see clause 4/		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	/2-2
6.2.1	Linear gain: value a specified bias conditions and t	G _{lin}	×		×				×		A4
6.2.2	Linear gain flatness: value at specified bias conditions and specified frequency range	$\Delta {m G}_{\sf lin}$		×		×				×	A4
6.2.3	Power gain: value at specified bias conditions, <i>f</i> and <i>P</i> _{in}	$G_{ m p}$			×				×		A4
6.2.4	Power gain flatness: value at specified bias conditions, specified frequency range and P _{in}	ΔG_{p}				×				×	A4
6.2.5	Gain reduction: value at specified bias conditions, <i>f</i> and AGC bias	$\Delta {\it G}_{ m red}$			×						A4
6.2.6	Limiting output power: value at specified bias conditions, f , P_{imin} and P_{imax}	$P_{o(Itg)}$					×	×			A4